AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

- 1. (original) A method for producing a substrate having a crystalline Si layer comprising the steps of forming an amorphous Si layer on a plastic substrate, and irradiating said amorphous Si layer with a laser beam to crystallize said amorphous Si, wherein said plastic substrate has light transmittance of 30 to 100% at an oscillation wavelength of said laser beam.
- 2. (original): The method of claim 1 for producing a substrate having a crystalline Si layer, wherein said amorphous Si layer has a thickness of 1 to 2000 nm.
- 3. (currently amended): The method of claim 1 or 2 for producing a substrate having a crystalline Si layer, wherein the oscillation wavelength of said laser beam is 140 to 450 nm.
- 4. (currently amended): The method of any one of claims 1 to 3 claim 1 for producing a substrate having a crystalline Si layer, wherein said laser is an excimer laser.
- 5. (currently amended): The method of any one of claims 1 to 4claim 1 for producing a substrate having a crystalline Si layer, wherein said plastic substrate is made of amorphous polyolefin or polyethersulfone.
- 6. (currently amended): The method of any one of claims 1 to 5claim 1 for producing a substrate having a crystalline Si layer, wherein said plastic substrate is made of a cycloolefin polymer represented by the following general formula (1):

or by the following general formula (2):

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wherein R¹ and R² independently represent a hydrogen atom, a nonpolar group, a halogen atom, a hydroxyl group, an ester group, an alkoxy group, a cyano group, an amide group, an imide group or a silyl group; n represents an integer of 1 to 100,000; and R¹ and R² may be connected to each other to form a mono- or poly-cyclic ring, provided that R¹ and R² do not form a 5-membered, unsubstituted, saturated, monocyclic hydrocarbon.

- 7. (currently amended): A substrate having a crystalline Si layer produced by the method recited in any one of claims 1 to 6 claim 1.
- 8. (original): The substrate of claim 7 having a crystalline Si layer, wherein said plastic substrate is provided with an insulating thin film having a thickness of 10 nm to 10 μ m on at least one surface.
- 9. (currently amended): A crystalline Si device comprising the substrate of claim 7 or 8 having a crystalline Si layer.